

# SHINDENGEN

## General Purpose Rectifiers

Dual

# S1ZA20

## 200V 1.1A

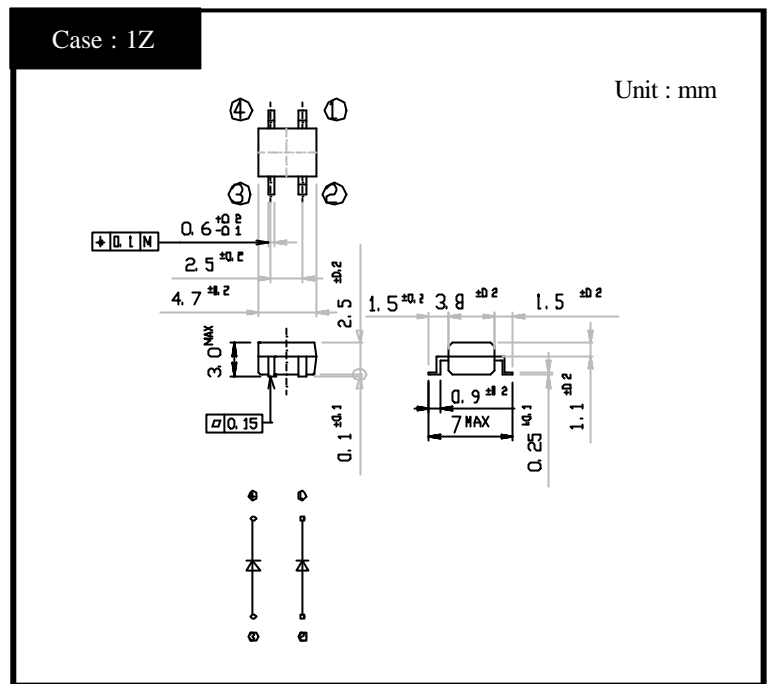
### FEATURES

- Small SMT package
- Array
- High reliability with superior moisture resistance
- Applicable to Automatic Insertion

### APPLICATION

- Conventional Rectification
- Motor
- Home Appliances, Office Equipment
- Telecommunication, Factory Automation

### OUTLINE DIMENSIONS



### RATINGS

Absolute Maximum Ratings (If not specified Tl=25 )

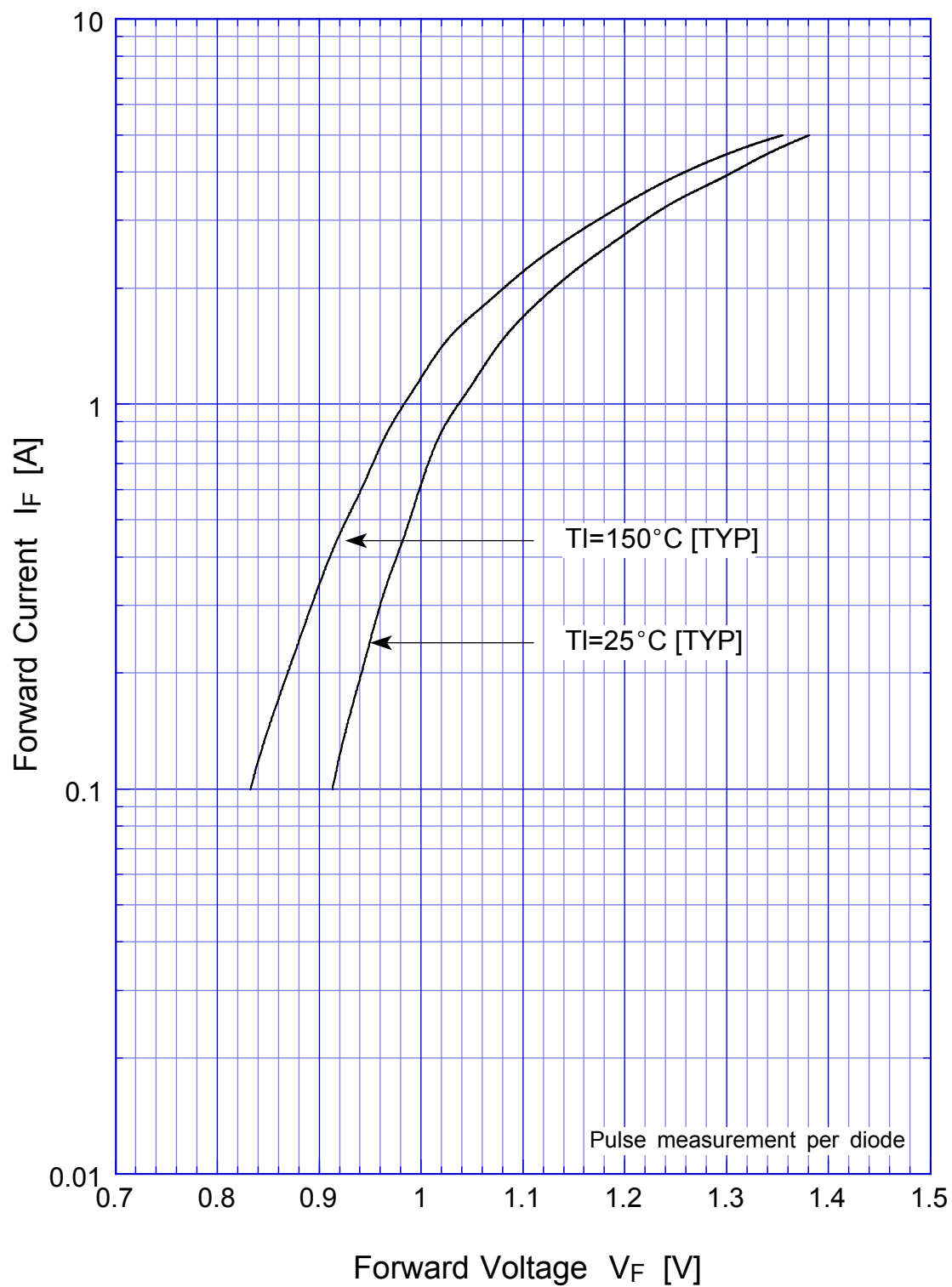
| Item                              | Symbol           | Conditions  | Ratings   | Unit |
|-----------------------------------|------------------|---|-----------|------|
| Storage Temperature               | Tstg             |   | -40 ~ 150 |      |
| Operating Junction Temperature    | Tj               |   | 150       |      |
| Maximum Reverse Voltage           | V <sub>RM</sub>  |   | 200       | V    |
| Average Rectified Forward Current | I <sub>O</sub>   | 50Hz sine wave, R-load Ta=25 On alumina substrate 1 element operation     | 1.1       | A    |
|                                   |                  | 50Hz sine wave, R-load Ta=25 On alumina substrate 2 element operation     | 0.8       |      |
|                                   |                  | 50Hz sine wave, R-load Ta=25 On glass-epoxy substrate 1 element operation | 0.9       |      |
|                                   |                  | 50Hz sine wave, R-load Ta=25 On glass-epoxy substrate 2 element operation | 0.63      |      |
| Peak Surge Forward Current        | I <sub>FSM</sub> | 50Hz sine wave, Non-repetitive 1cycle peak value, Tj=25                   | 30        | A    |

Electrical Characteristics (If not specified Tl=25 )

| Item               | Symbol         | Conditions   | Ratings | Unit |
|--------------------|----------------|--|---------|------|
| Forward Voltage    | V <sub>F</sub> | IF=0.9A, Pulse measurement, Rating of per diode                          | Max.1.1 | V    |
| Reverse Current    | I <sub>R</sub> | V <sub>R</sub> =V <sub>RM</sub> , Pulse measurement, Rating of per diode | Max.10  | μA   |
| Thermal Resistance | ja             | junction to ambient On alumina substrate 1 element operation             | Max.93  | /W   |
|                    |                | junction to ambient On alumina substrate 2 element operation             | Max.140 |      |
|                    |                | junction to ambient On glass-epoxy substrate 1 element operation         | Max.120 |      |
|                    |                | junction to ambient On glass-epoxy substrate 2 element operation         | Max.186 |      |

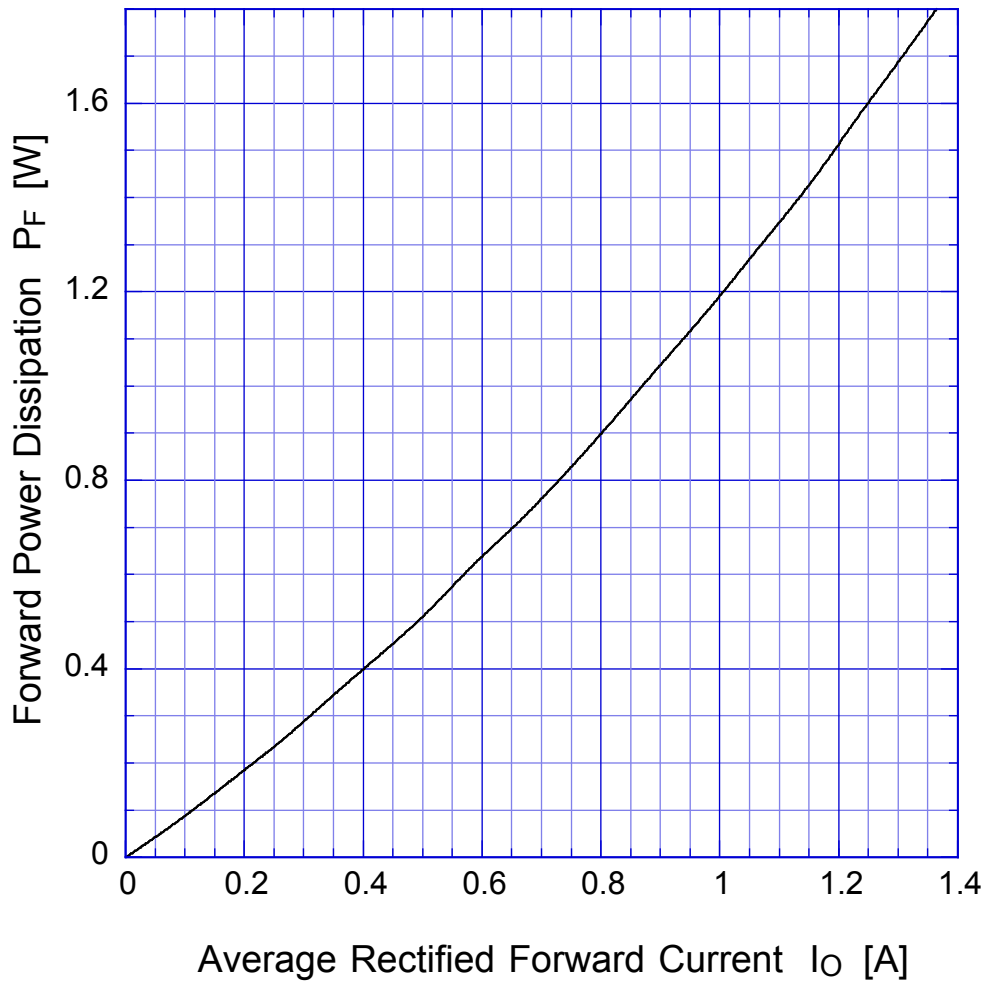
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Forward Voltage



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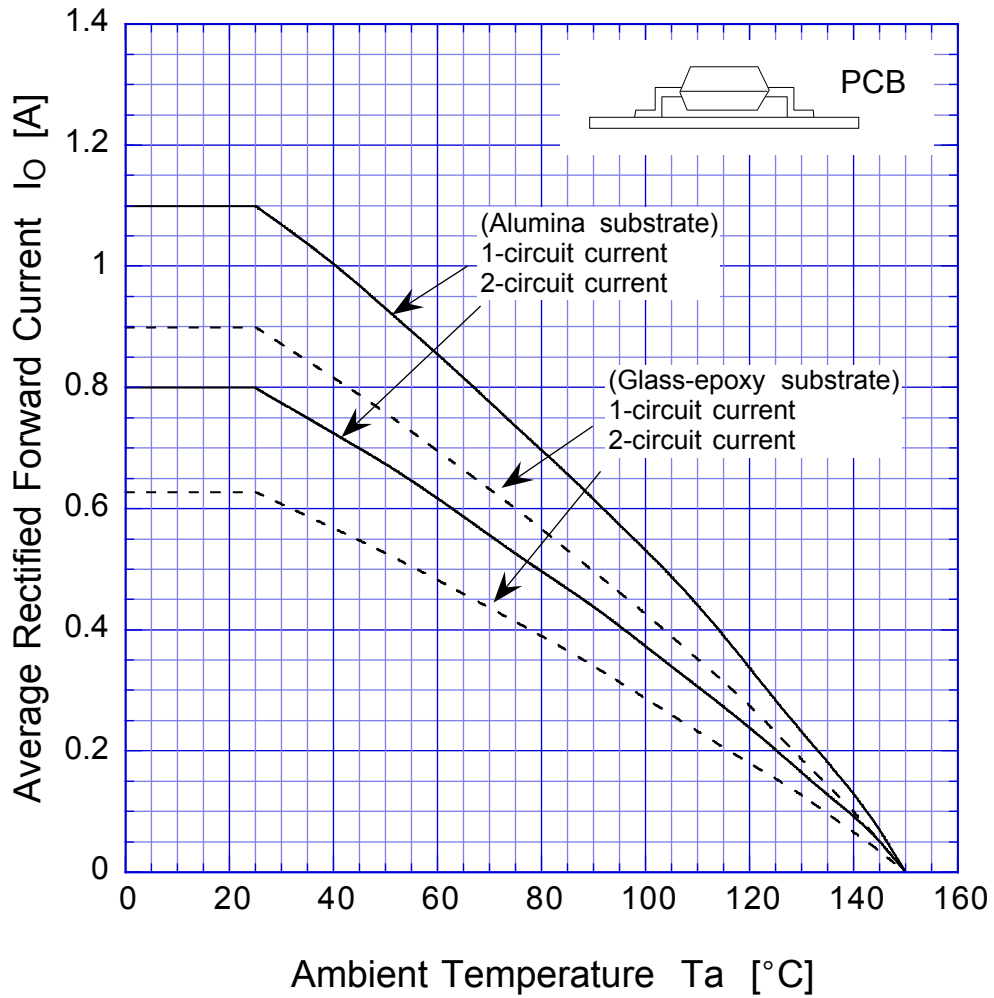
Forward Power Dissipation



$T_j = 150^\circ\text{C}$   
Sine wave

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## Derating Curve



Alumina substrate  
Soldering land 1mm  
Conductor layer 20 $\mu$ m  
Substrate thickness 0.64mm

Glass-epoxy substrate  
Soldering land 1mm  
Conductor layer 35 $\mu$ m

Sine wave  
R-load  
Free in air

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## Peak Surge Forward Capability

